

### **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

## 25N10

<ul> <li>High sp</li> <li>Standa</li> <li>Easy to</li> <li>100% a</li> <li>Minimu</li> </ul>	D-252(DPAK) packaging beed switching rd level gate drive	PIN 1.Gate 2.Drain 3.Source TO-252 package			
	CATIONS				и Aи С 0.5
	supply ng applications -UTE MAXIMUM RATING	2(T -25°C)			
SYMBOL	PARAMETER	5(1a-25 C)	VALUE	UNIT	D
V <sub>DSS</sub>	Drain-Source Voltage		100	V	
V <sub>GSS</sub>	Gate-Source Voltage		±20	V	
ID	Drain Current-Continuous	Tc=25℃ Tc=100℃	23 14.6	А	
I <sub>DM</sub>	Drain Current-Single Pulsed		80	А	
PD	Total Dissipation		41	W	
Tj	Operating Junction Temperati	ıre	-55~150	°C	mm
	Operating Junction Temperate Storage Temperature	ıre	-55~150 -55~150	°	DIM MIN MAX A 6.40 6.60
Tj Tstg		ıre			DIM         MIN         MAX           A         6.40         6.60           B         5.20         5.40           C         1.15         1.35           D         5.70         6.10
Tj Tstg	Storage Temperature				DIM         MIN         MAX           A         6.40         6.60           B         5.20         5.40           C         1.15         1.35           D         5.70         6.10           F         0.65           G         0.75
Tj Tstg • THERN	Storage Temperature	ER	-55~150	°C	DIM         MIN         MAX           A         6.40         6.60           B         5.20         5.40           C         1.15         1.35           D         5.70         6.10           F         0.65           G         0.75

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#### **ELECTRICAL CHARACTERISTICS**

#### $T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 1mA	100			v
V <sub>GS</sub> (th)	Gate Threshold Voltage V <sub>DS</sub> =10V; I <sub>D</sub> =0.25mA		2		4	v
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =16A			80	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V			±0.1	μ Α
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 100V; V <sub>GS</sub> = 0V;Tj=25℃ Tj=100℃			25 100	μ Α
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =16A, V <sub>GS</sub> = 0 V			1.3	V

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